

IGBT Module

SK50GD066ET

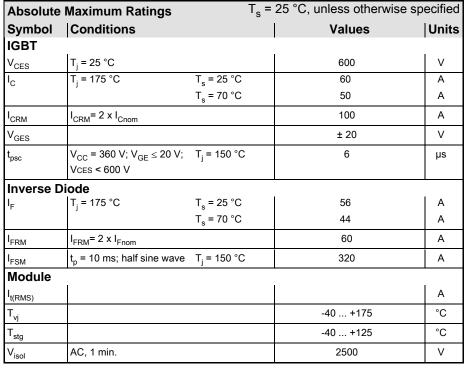
Target Data

Features

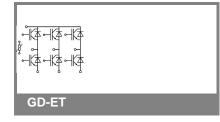
- Compact design
- · One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- · Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications*

- Inverter up to 12,5 kVA
- Typ. motor power 5,5 kW



Characteristics T _s = 25 °C, unless otherwise speci						
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 0.8 \text{ mA}$		5	5,8	6,5	V
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES}	T _j = 25 °C				mA
		T _j = 150 °C				mA
I _{GES}	V _{CE} = 0 V, V _{GE} = 20 V	T _j = 25 °C			600	nA
		T _j = 150 °C				nA
V _{CE0}		T _j = 25 °C		0,9	1,1	V
		T _j = 150 °C		0,8	1	V
r _{CE}	V _{GE} = 15 V	T _j = 25°C		11	15	mΩ
		T _j = 150°C		17	21	mΩ
V _{CE(sat)}	I _{Cnom} = 50 A, V _{GE} = 15 V			1,45	1,85	V
		$T_j = 150^{\circ}C_{chiplev.}$		1,65	2,05	V
C _{ies}				3,1		nF
C _{oes}	$V_{CE} = 25, V_{GE} = 0 V$	f = 1 MHz		0,2		nF
C _{res}				0,093		nF
Q_G	V _{GE} = -7V+15V			250		nC
t _{d(on)}				28		ns
t _r E _{on}	$R_{Gon} = 16 \Omega$	V _{CC} = 300V		32		ns
E _{on}	di/dt = 2438 A/µs	I _C = 50A		2,2		mJ
^L d(off)	$R_{Goff} = 16 \Omega$	T _j = 150 °C		301		ns
Гf	di/dt = 2438 A/µs	V _{GE} = -7/+15V		45		ns
E _{off}				1,73		mJ
$R_{th(j-s)}$	per IGBT			1,11		K/W





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Inverse D	iode								
$V_F = V_{EC}$	I_{Fnom} = 50 A; V_{GE} = 0 V			1,5		V			
		T _j = 150 °C _{chiplev.}		1,5		V			
V _{F0}		T _j = 25 °C		1	1,1	V			
		T _j = 150 °C		0,9	1	V			
r _F		T _j = 25 °C		10	12	mΩ			
		T _j = 150 °C		12	14	$m\Omega$			
I _{RRM}	I _F = 50 A	T _j = 150 °C		44		Α			
Q_{rr}	di/dt = 2438 A/µs			4,8		μC			
E _{rr}	V _{CC} = 300V			0,72		mJ			
$R_{th(j-s)D}$	per diode			1,7		K/W			
M _s	to heat sink		2,25		2,5	Nm			
w				30		g			
Temperature sensor									
R ₁₀₀	T_s =100°C (R_{25} =5kΩ)			493±5%		Ω			

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

